

# Jeffrey A Maharrey

## List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Angular Effects on Single-Event Mechanisms in Bulk FinFET Technologies. IEEE Transactions on Nuclear Science, 2018, 65, 223-230.	2.0	24
2	Effect of Device Variants in 32Ånm and 45Ånm SOI on SET Pulse Distributions. IEEE Transactions on Nuclear Science, 2013, 60, 4399-4404.	2.0	21
3	The Impact of Charge Collection Volume and Parasitic Capacitance on SEUs in SOI- and Bulk-FinFET D Flip-Flops. IEEE Transactions on Nuclear Science, 2018, 65, 326-330.	2.0	20
4	Geometry-Aware Single-Event Enabled Compact Models for Sub-50Ånm Partially Depleted Silicon-on-Insulator Technologies. IEEE Transactions on Nuclear Science, 2015, 62, 1589-1598.	2.0	17
5	Estimating Single-Event Logic Cross Sections in Advanced Technologies. IEEE Transactions on Nuclear Science, 2017, , 1-1.	2.0	17
6	Effect of Transistor Variants on Single-Event Transients at the 14-/16-nm Bulk FinFET Technology Generation. IEEE Transactions on Nuclear Science, 2018, 65, 1807-1813.	2.0	16
7	Impact of Single-Event Transient Duration and Electrical Delay at Reduced Supply Voltages on SET Mitigation Techniques. IEEE Transactions on Nuclear Science, 2018, 65, 362-368.	2.0	14
8	Exploiting Parallelism and Heterogeneity in a Radiation Effects Test Vehicle for Efficient Single-Event Characterization of Nanoscale Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 486-494.	2.0	13
9	Dual-Interlocked Logic for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2018, 65, 1872-1878.	2.0	13
10	A Bias-Dependent Single-Event-Enabled Compact Model for Bulk FinFET Technologies. IEEE Transactions on Nuclear Science, 2019, 66, 635-642.	2.0	9
11	Single-Event Response of 22-nm Fully Depleted Silicon-on-Insulator Static Random Access Memory. IEEE Transactions on Nuclear Science, 2021, 68, 402-409.	2.0	9
12	Empirical Modeling of FinFET SEU Cross Sections Across Supply Voltage. IEEE Transactions on Nuclear Science, 2019, 66, 1427-1432.	2.0	8
13	Heavy-Ion Induced SETs in 32nm SOI Inverter Chains. , 2015, , .		3
14	Exploiting SEU Data Analysis to Extract Fast SET Pulses. IEEE Transactions on Nuclear Science, 2019, 66, 932-937.	2.0	1